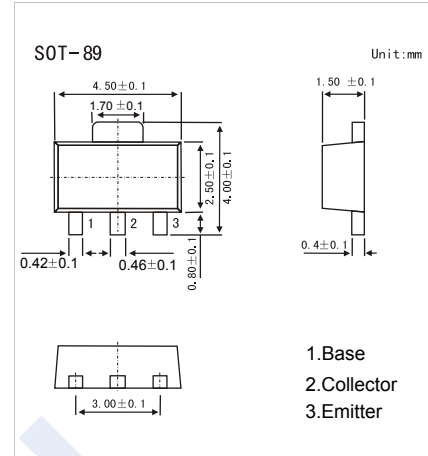


PNP Transistors

2SA1681

■ Features

- Low saturation voltage
- High speed switching time
- Small flat package
- PC = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SC4409



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CEO}	-50	
Emitter - Base Voltage	V _{EB0}	-6	
Collector Current - Continuous	I _C	-2	A
Base Current	I _B	-0.2	
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E = 0	-60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B = 0	-50			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C = 0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -60 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -6 V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -1 A, I _B = -50 mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -1 A, I _B = -50 mA			-1.2	
DC current gain	h _{FE(1)}	V _{CE} = -2V, I _C = -100 mA	120		400	
	h _{FE(2)}	V _{CE} = -2V, I _C = -1.5 A	40			
Turn-on time	t _{on}			0.1	μs	
Storage time	t _{stg}					0.3
Fall time	t _f					0.1
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		23		pF
Transition frequency	f _T	V _{CE} = -2V, I _C = -100 mA		100		MHz

■ Marking

Marking	L*A
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Typical Characteristics

